

IN THE DRAWINGS:

Enclosed herein is a Replacement Sheet of formal drawing Figures 1-2, which have been amended to include a "Conventional Art" legend.

REMARKS

Claims 15-18 are pending. By this Amendment, Claims 15-18 are amended. As support for the amendments is provided in the originally filed application, such as, for example only, page 7, line 26 to page 9, line 18, Applicants respectfully submit that no new matter is presented herein.

Specification

The Specification is objected to for an informality therein. Applicants have amended the Specification herein to be responsive to the objection. Withdrawal of the objection is respectfully requested.

Drawings

The Drawings are objected to because only that which is old is illustrated. Enclosed herein is a Replacement Sheet of formal drawing Figures 1-2, which have been amended to include a "Conventional Art" legend to be responsive to the objection. Withdrawal of the objection is respectfully requested.

Claim Rejections – 35 U.S.C. §112

Claims 15-18 are rejected under 35 U.S.C. §112, second paragraph. Applicants respectfully submit the claims have been amended responsive to the rejection. Withdrawal of the rejection is respectfully requested.

Claim Rejections – 35 U.S.C. §102

Claims 15-18 are rejected under 35 U.S.C. §102(b) as being anticipated by U.S. Patent No. 5,629,114 to Isao et al. (Isao). Applicants respectfully traverse the rejection.

Claims 15-18 each recite a method for manufacturing a semiconductor circuit, including, among other features, wherein a relative flow rate of the mixed gas used consists of, by volume of mixed gas, one of: 1) chlorine, oxygen and hydrogen gases from 66 to 46%, 17 to 11%, and 18 to 41%, respectively; and 2) chlorine, oxygen and hydrogen chloride gases from 58 to 44%, 15 to 11%, and 28 to 45%, respectively for etching is 17 to 11% by volume of the mixed gas. As clearly stated in the originally filed Specification, if the flow rate exceeds the cited range, it is difficult to obtain a highly precise half-tone phase shift mask having reduced dimensional differences due to the coexistence of coarse and dense patterns in a plane. See, for example, the paragraph on page 11, lines 12-25 of the originally filed application.

Applicants respectfully submit Isao fails to disclose or suggest such a feature. In fact, Applicants have reviewed Isao in detail and are unable to locate any disclosure or suggestion of a flow rate for the oxygen-containing gas of the reactive ion etching gas.

To qualify as prior art under 35 USC 102, a single reference must teach, i.e., identically describe, each feature of a rejected claim. As explained above, Isao does not disclose or suggest each and every feature recited by pending Claims 15-18. Therefore, Isao does not anticipate or render obvious the subject matter recited by Claims 15-18. Accordingly, Applicants respectfully submit independent Claims 15-18 should be deemed allowable over Isao.

Applicants respectfully request withdrawal of the rejection.

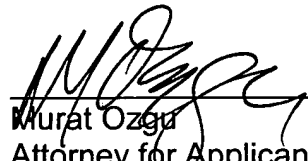
Conclusion

In view of the foregoing, reconsideration of the application, withdrawal of the outstanding objections and rejections, allowance of Claims 15-18, and the prompt issuance of a Notice of Allowability are respectfully solicited.

Should the Examiner believe anything further is desirable in order to place this application in better condition for allowance, the Examiner is requested to contact the undersigned at the telephone number listed below.

In the event this paper is not considered to be timely filed, the Applicants respectfully petition for an appropriate extension of time. Any fees for such an extension, together with any additional fees that may be due with respect to this paper, may be charged to counsel's Deposit Account No. 01-2300, **referencing attorney docket number 101136-00102.**

Respectfully submitted,



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Enclosure: Replacement Sheet of Formal Drawing Figures 1-2

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